

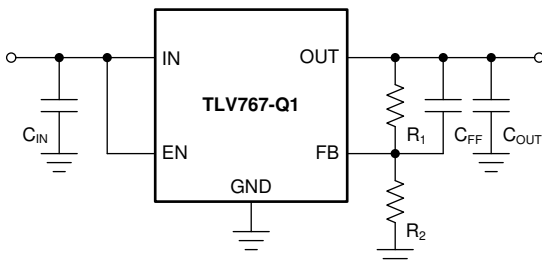
TLV767-Q1 1A、16V リニア電圧レギュレータ

1 特長

- 車載アプリケーション用に AEC-Q100 認定取得済み
 - 温度グレード 1: $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$ 、 T_A
 - 接合部温度: $-40^{\circ}\text{C} \sim +150^{\circ}\text{C}$ 、 T_J
- 入力電圧範囲: 2.5V ~ 16V (最大 18V)
- 出力電圧範囲:
 - 0.8V ~ 14.6V (可変)
 - 1.2V ~ 12V (固定)
- 負荷および温度範囲にわたって 1% の出力精度
- 低い静止電流 (I_Q):
 - 無負荷時: 50 μA (標準値)
 - デイスレーブル時: 4 μA 以下
- 高 PSRR: 1kHz で 70dB、1MHz で 46dB
- 内部ソフトスタート時間: 500 μs (標準値)
- フォールドバック電流制限および過熱保護
- 1 μF 以上のコンデンサで安定
- パッケージ: 8 ピン、3mm \times 3mm ウェットابل・フランク WSON
 - 低い熱抵抗 ($R_{\theta JA}$): 51.9 $^{\circ}\text{C}/\text{W}$

2 アプリケーション

- DC/DC コンバータ
- インバータおよびモータ制御
- オンボード・チャージャ (OBC) とワイヤレス・チャージャ
- 車載ヘッド・ユニット



代表的なアプリケーション回路

3 概要

TLV767-Q1 は入力範囲の広いリニア電圧レギュレータで、2.5V ~ 16V の入力電圧範囲に対応し、最大 1A の負荷電流を供給できます。出力範囲は 0.8V ~ 12V、または可変バージョンでは最高 14.6V です。

入力電圧範囲が広いこと、変圧器の 2 次巻線やレギュレートされた 10V または 12V などのレールに適しています。また、出力電圧範囲も広いこと、シリコン・カーバイド (SiC) ゲート・ドライバやマイク用のバイアス電圧を生成したり、マイクロコントローラ (MCU) やプロセッサに電力供給できます。

TLV767-Q1 は、電源要件の厳しいデジタル負荷への電力供給が必要とされる出力精度 1% を達成しています。

内蔵するソフトスタート回路により、スタートアップ時の突入電流が抑制されるため、入力容量の低減が可能です。

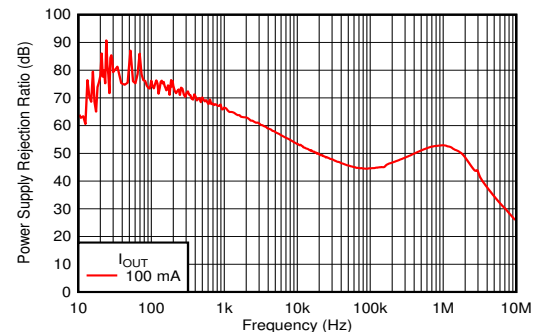
広帯域の PSRR 特性は、1kHz で 70dB、1MHz で 46dB を超え、上流の DC/DC コンバータのスイッチング周波数を減衰して、レギュレータ後のフィルタ処理を最小化できます。20Hz ~ 20kHz で高いリップル除去比を実現しており、オーディオ部品への電力供給に最適です。

TLV767-Q1 はウェットابل・フランクを採用した、熱抵抗の小さい 8 ピン、3mm \times 3mm VSON (DRB) パッケージで供給されます。

製品情報 (1) (1 ページ)

型番	パッケージ	本体サイズ (公称)
TLV767-Q1	VSON (8)	3.00mm \times 3.00mm

(1) 利用可能なすべてのパッケージについては、このデータシート末尾にある注文情報を参照してください。



PSRR 性能



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (April 2020) to Revision A (December 2020)	Page
• ドキュメントのステータスを事前情報から量産データに変更.....	1

5 Pin Configuration and Functions

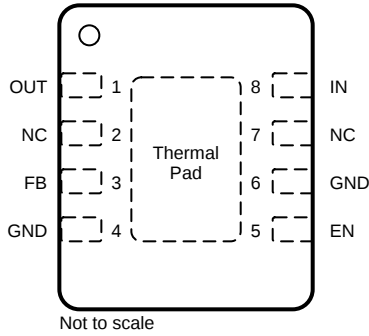


图 5-1. DRB Package (Adjustable Version), 8-Pin WSON, Top View

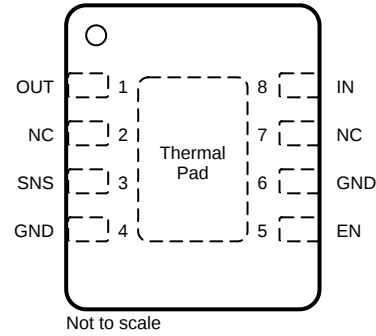


图 5-2. DRB Package (Fixed Version), 8-Pin WSON, Top View

表 5-1. Pin Functions

NAME	PIN		I/O	DESCRIPTION
	DRB (Adjustable)	DRB (Fixed)		
EN	5	5	Input	Enable pin. Driving the enable pin high enables the device. Driving this pin low disables the device. High and low thresholds are listed in the <i>Electrical Characteristics</i> table. This pin has an internal pullup resistor and can be left floating to enable the device or the pin can be connected to the input pin.
FB	3	—	Input	Feedback pin. Input to the control-loop error amplifier. This pin is used to set the output voltage of the device with the use of external resistors. Do not float this pin. For adjustable-voltage version devices only.
GND	4, 6	4, 6	—	Ground pin. All ground pins must be grounded.
NC	2, 7	2, 7	—	NC pin. Not internally connected. This pin can be either floated or connected to GND for best thermal performance.
IN	8	8	Input	Input pin. Use the recommended capacitor value as listed in the <i>Recommended Operating Conditions</i> table. Place the input capacitor as close to the IN and GND pins of the device as possible.
OUT	1	1	Output	Output pin. Use the recommended capacitor value as listed in the <i>Recommended Operating Conditions</i> table. Place the output capacitor as close to the OUT and GND pins of the device as possible.
SNS	—	3	Input	Output sense pin. Connect the SNS pin to the OUT pin, or to remotely sense the output voltage at the load, connect the SNS pin to the load. Do not float this pin. For fixed-voltage version devices only.
Thermal pad			—	Exposed pad of the package. Connect this pad to ground or leave floating. Connect the thermal pad to a large-area ground plane for best thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Voltage ⁽²⁾	Input pin, IN	-0.3	18	V
	Output pin, OUT ⁽³⁾	-0.3	$V_{IN} + 0.3$	
	Sense pin, SNS ⁽³⁾	-0.3	$V_{IN} + 0.3$	
	Feedback pin, FB	-0.3	3	
	Enable pin, EN	-0.3	18	
Current	Maximum output current	Internally limited		A
Temperature	Ambient (T_A)	-40	125	°C
	Operating junction (T_J)	-50	150	
	Storage (T_{STG})	-65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages with respect to GND.
- (3) $V_{IN} + 0.3$ V or 18 V (whichever is smaller).

6.2 ESD Ratings

			VALUE	UNIT	
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V	
		Charged-device model (CDM), per AEC Q100-011	All pins		±500
			Corner pins		±750

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	Input voltage	2.5		16	V
V _{EN}	Enable voltage	0		16	V
V _{OUT}	Output voltage	0.8		14.6	V
I _{OUT}	Output current	0		1	A
C _{OUT}	Output capacitor ⁽¹⁾	1	2.2	220	μF
C _{OUT ESR}	Output capacitor ESR	2		500	mΩ
C _{IN}	Input capacitor		1		μF
C _{FF}	Feed-forward capacitor (optional ⁽²⁾ , for adjustable device only)		10		pF
I _{FB_DIVIDER}	Feedback divider current ⁽²⁾ (adjustable device only)	5			μA
T _A	Ambient temperature range	–40		125	°C
T _J	Junction temperature range	–40		150	°C

- (1) Effective output capacitance of 0.5 μF minimum required for stability.
 (2) C_{FF} required for stability if the feedback divider current < 5 μA. Feedback divider current = V_{OUT} / (R₁ + R₂). See the *Feed-Forward Capacitor (C_{FF})* section for details.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV767-Q1	UNIT
		DRB (VSON)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	51.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	66.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	24.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	2.7	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	24.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	6.9	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

specified at $T_J = -40^\circ\text{C}$ to 150°C , $V_{IN} = V_{OUT(nom)} + 1.5\text{ V}$ or $V_{IN} = 2.5\text{ V}$ (whichever is greater), FB/SNS tied to OUT, $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted); typical values are at $T_J = 25^\circ\text{C}$

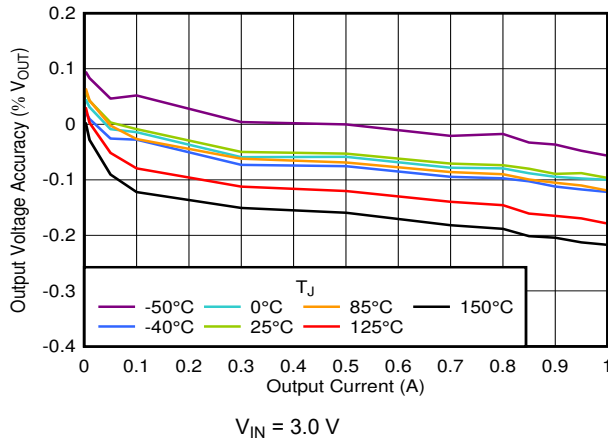
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OUT}	Output accuracy	$T_J = 25^\circ\text{C}$		-0.5		0.5	%
		$T_J = -40^\circ\text{C}$ to 150°C	$V_{IN} \geq 3.0\text{ V}$, $1\text{ mA} \leq I_{OUT} \leq 1\text{ A}$	-1		1	%
			$2.5\text{ V} \leq V_{IN} < 3.0\text{ V}$, $1\text{ mA} \leq I_{OUT} \leq 800\text{ mA}$	-1		1	%
V_{FB}	Feedback voltage				0.8		V
V_{REF}	Internal reference (adjustable device)	$T_J = 25^\circ\text{C}$		-0.5		0.5	%
		$T_J = -40^\circ\text{C}$ to 150°C		-1		1	
I_{FB}	Feedback pin current	$V_{FB} = 1\text{ V}$		-20	1	50	nA
$\Delta V_{OUT(\Delta V_{IN})}$	Line regulation ⁽¹⁾	$V_{OUT(NOM)} + 1.5\text{ V} \leq V_{IN} \leq 16\text{ V}$, $I_{OUT} = 10\text{ mA}$				0.02	%/V
$\Delta V_{OUT(\Delta I_{OUT})}$	Load regulation	$1\text{ mA} \leq I_{OUT} \leq 1\text{ A}$, $V_{IN} \geq 3.0\text{ V}$			0.1	0.5	%/A
		$1\text{ mA} \leq I_{OUT} \leq 800\text{ mA}$, $2.5\text{ V} \leq V_{IN} < 3.0\text{ V}$			0.1	0.5	
V_{DO}	Dropout voltage ⁽²⁾	$V_{IN(NOM)} \geq 3.0\text{ V}$, $I_{OUT} = 1\text{ A}$		0.63	0.94	1.5	V
		$2.5\text{ V} \leq V_{IN(NOM)} < 3.0\text{ V}$, $I_{OUT} = 800\text{ mA}$		0.48	0.8	1.4	
I_{CL}	Output current limit	$V_{OUT} = 0.9 \times V_{OUT(NOM)}$, $V_{IN} \geq 3.0\text{ V}$		1.1	1.37	1.6	A
		$V_{OUT} = 0.9 \times V_{OUT(NOM)}$, $2.5\text{ V} \leq V_{IN} < 3.0\text{ V}$		0.81	1.28	1.6	
I_{SC}	Short-circuit current limit	$V_{OUT} = 0\text{ V}$		150	250	350	mA
I_Q	Quiescent current	Adjustable output device, $I_{OUT} = 0\text{ mA}$		25	50	80	μA
		Fixed output devices, $I_{OUT} = 0\text{ mA}$		25	60	95	
I_{GND}	Ground current	$I_{OUT} = 1\text{ A}$, $V_{IN} \geq 3.0\text{ V}$			1.5		mA
$I_{SHUTDOWN}$	Shutdown current	$V_{EN} \leq 0.4\text{ V}$, $V_{IN} = 16\text{ V}$		0.1	1.6	4	μA
$V_{EN(HIGH)}$	Enable pin logic high	$2.5\text{ V} \leq V_{IN} \leq 16\text{ V}$		1.2			V
$V_{EN(LOW)}$	Enable pin logic low	$2.5\text{ V} \leq V_{IN} \leq 16\text{ V}$				0.4	V
I_{EN}	Enable pullup current	$V_{EN} = 0\text{ V}$		200	400	800	nA
$I_{PULLDOWN}$	Output pulldown current	$V_{IN} = 16\text{ V}$, $V_{OUT} = 2.5\text{ V}$, $V_{EN} = 0\text{ V}$		0.9	1.4	1.6	mA
PSRR	Power-supply rejection ratio	$V_{IN} = 3.3\text{ V}$, $V_{OUT} = 1.8\text{ V}$, $I_{OUT} = 300\text{ mA}$, $f = 120\text{ Hz}$			70		dB
V_n	Output noise voltage	BW = 10 Hz to 100 kHz, $V_{IN} = 3.3\text{ V}$, $V_{OUT} = 0.8\text{ V}$, $I_{OUT} = 100\text{ mA}$			60		μV_{RMS}
V_{UVLO+}	UVLO threshold rising	V_{IN} rising		2	2.22	2.4	V
V_{UVLO-}	UVLO threshold falling	V_{IN} falling		1.9	2.09	2.3	V
$V_{UVLO(HYS)}$	UVLO hysteresis			100	130	200	mV
$T_{SD(shutdown)}$	Thermal shutdown temperature	Temperature increasing			180		$^\circ\text{C}$
$T_{SD(reset)}$	Thermal shutdown reset temperature	Temperature falling			160		$^\circ\text{C}$

(1) Line regulation is measured with $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater).

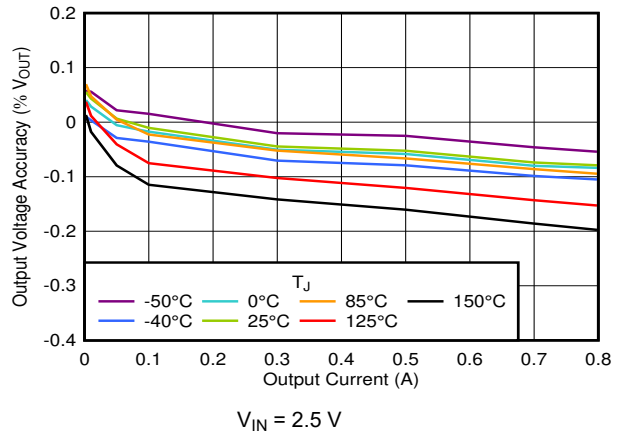
(2) V_{DO} is measured with $V_{IN} = 95\% \times V_{OUT(nom)}$ for fixed output devices. V_{DO} is not measured for fixed output devices when $V_{OUT} < 2.5\text{ V}$. For the adjustable output device, V_{DO} is measured with $V_{FB} = 95\% \times V_{FB(nom)}$.

6.6 Typical Characteristics

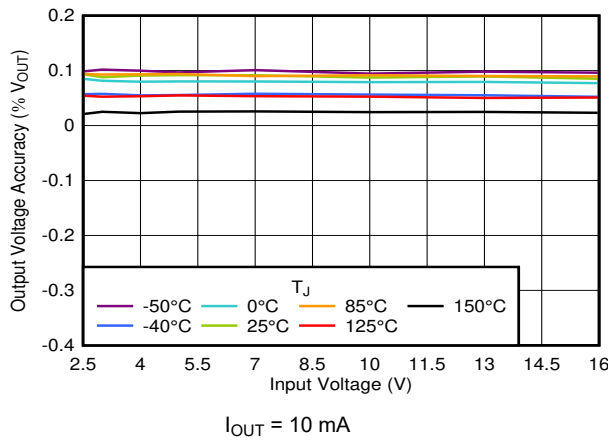
at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)



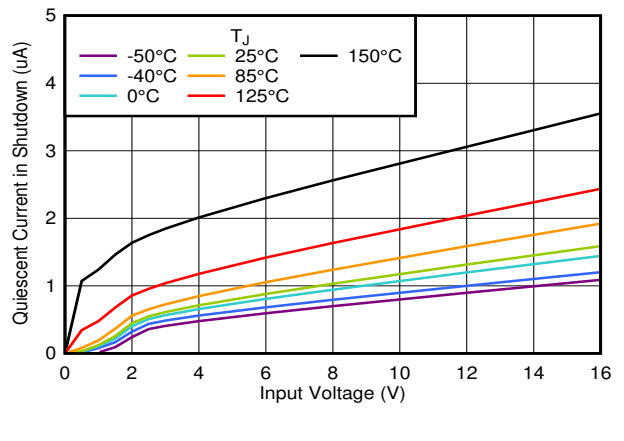
6-1. V_{OUT} Accuracy vs I_{OUT}



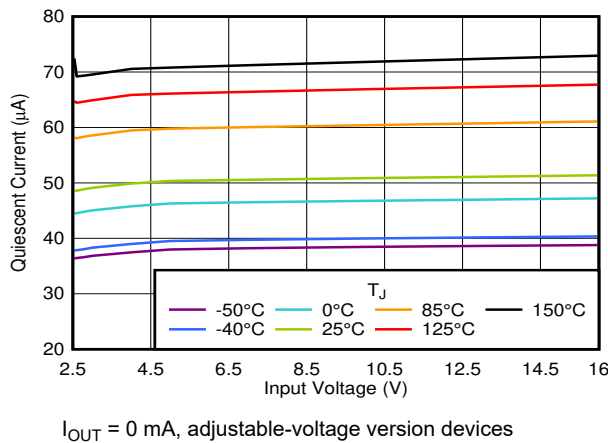
6-2. V_{OUT} Accuracy vs I_{OUT}



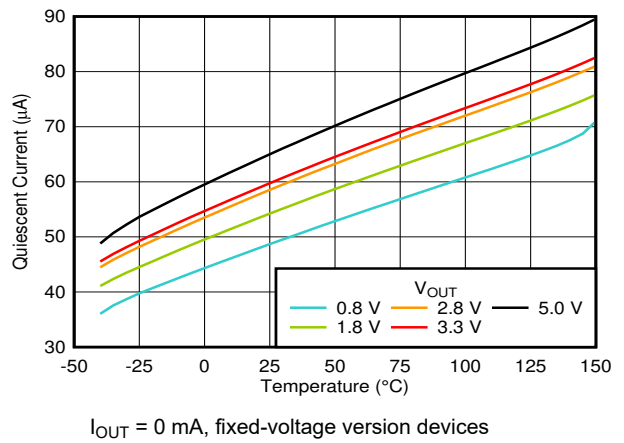
6-3. V_{OUT} Accuracy vs V_{IN}



6-4. $I_{SHUTDOWN}$ vs V_{IN}



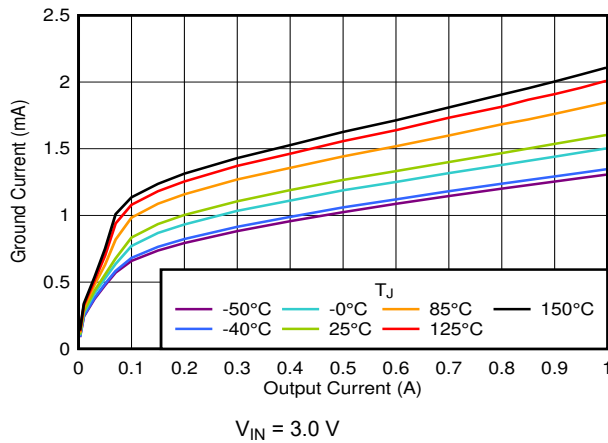
6-5. I_Q vs V_{IN}



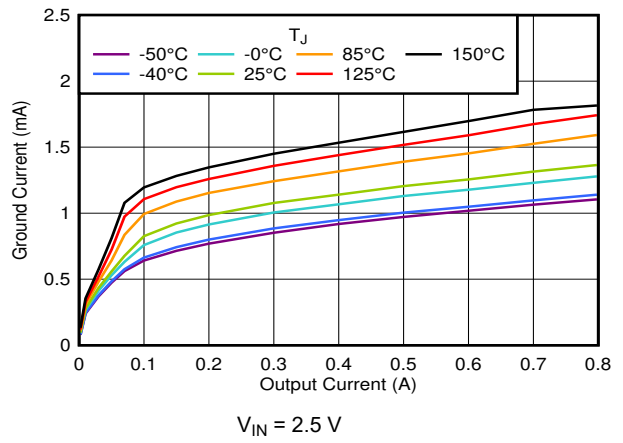
6-6. I_Q vs Temperature

6.6 Typical Characteristics (continued)

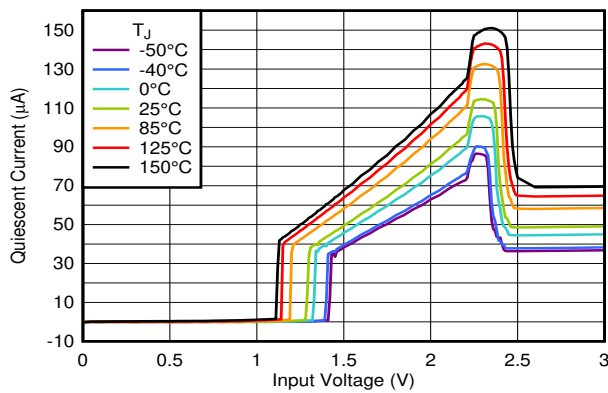
at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)



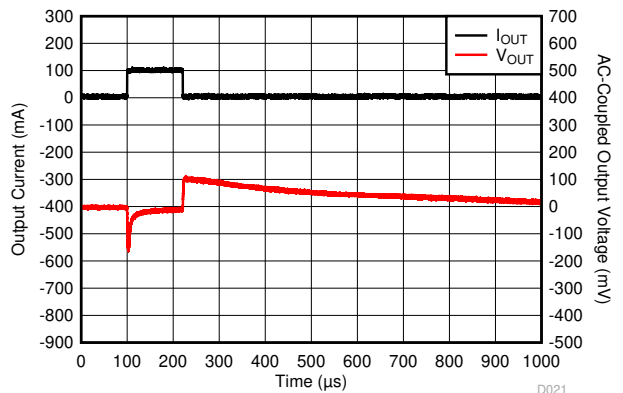
6-7. I_{GND} vs I_{OUT}



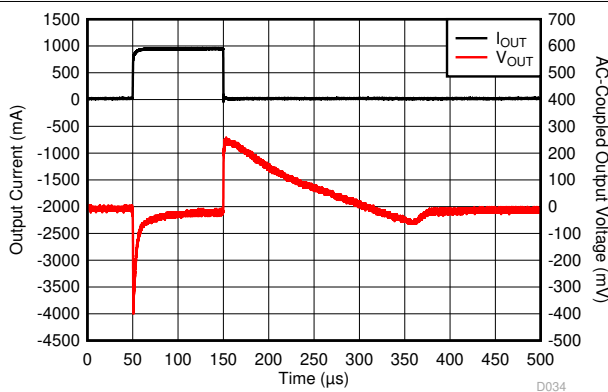
6-8. I_{GND} vs I_{OUT}



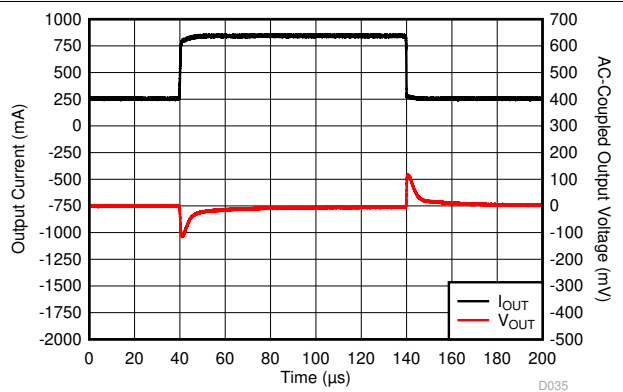
6-9. I_Q Increase Below Minimum V_{IN}



6-10. I_{OUT} Transient From 0 mA to 100 mA



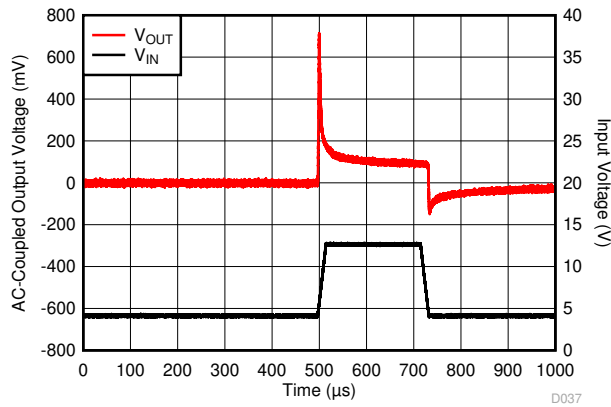
6-11. I_{OUT} Transient From 1 mA to 1 A



6-12. I_{OUT} Transient From 250 mA to 850 mA

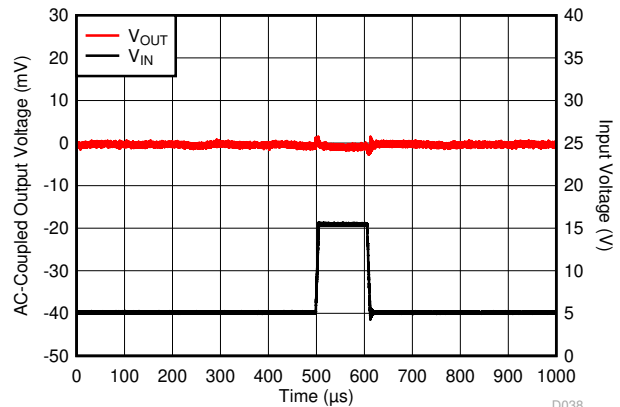
6.6 Typical Characteristics (continued)

at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)



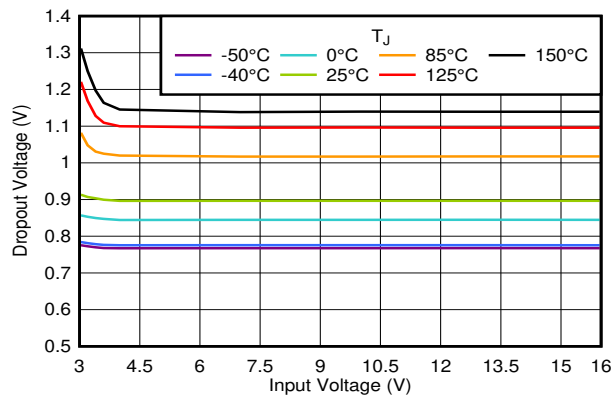
$V_{OUT} = 3.3\text{ V}$, $I_{OUT} = 1\text{ A}$, V_{IN} ramp rate = $0.6\text{ V}/\mu\text{s}$

6-13. V_{IN} Transient in Dropout From 4 V to 13 V



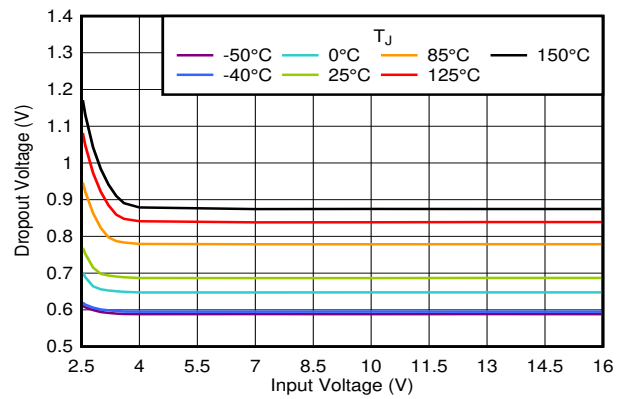
$V_{OUT} = 3.3\text{ V}$, $I_{OUT} = 33\text{ }\mu\text{A}$, V_{IN} ramp rate = $1.6\text{ V}/\mu\text{s}$

6-14. V_{IN} Transient From 5 V to 16 V



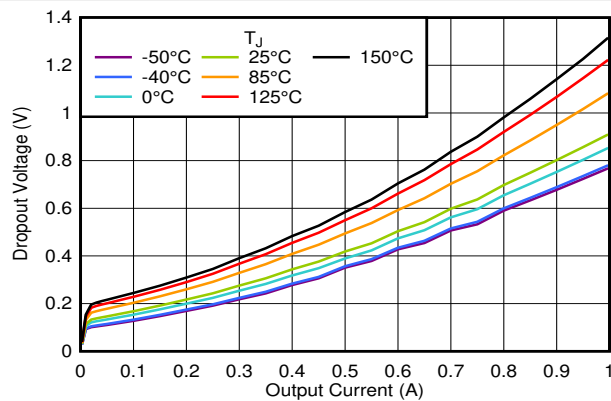
$I_{OUT} = 1.0\text{ A}$

6-15. V_{DO} vs V_{IN}



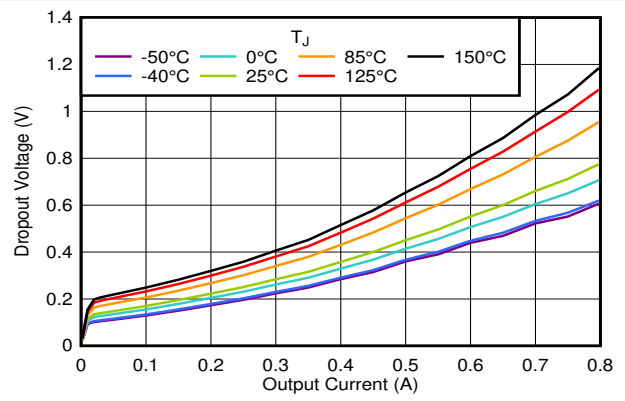
$I_{OUT} = 0.8\text{ A}$

6-16. V_{DO} vs V_{IN}



$V_{IN} = 3.0\text{ V}$

6-17. V_{DO} vs I_{OUT}

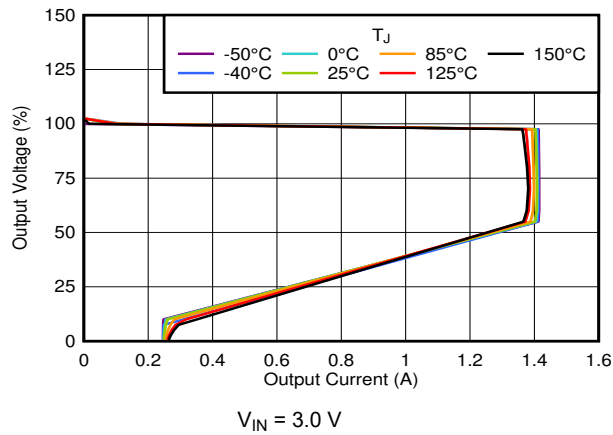


$V_{IN} = 2.5\text{ V}$

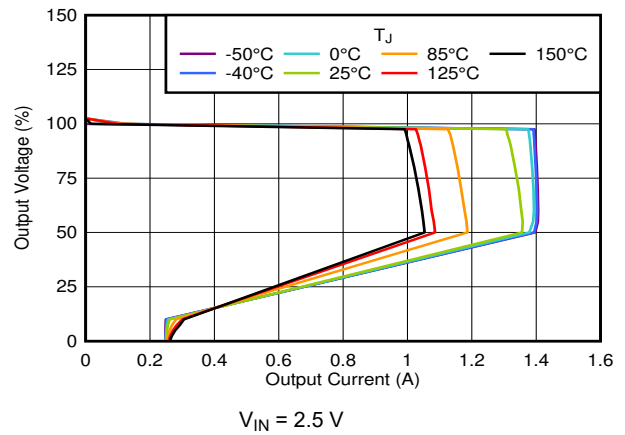
6-18. V_{DO} vs I_{OUT}

6.6 Typical Characteristics (continued)

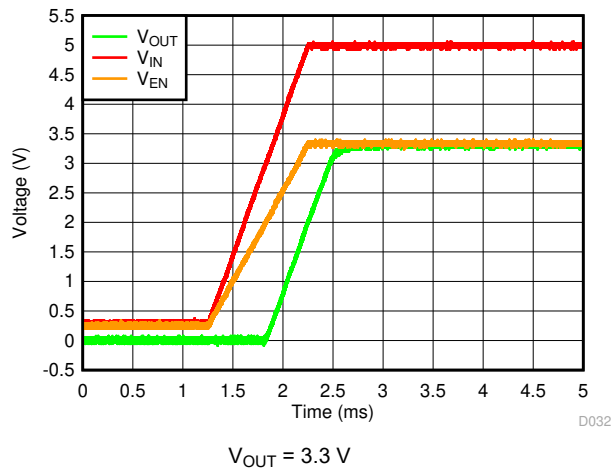
at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)



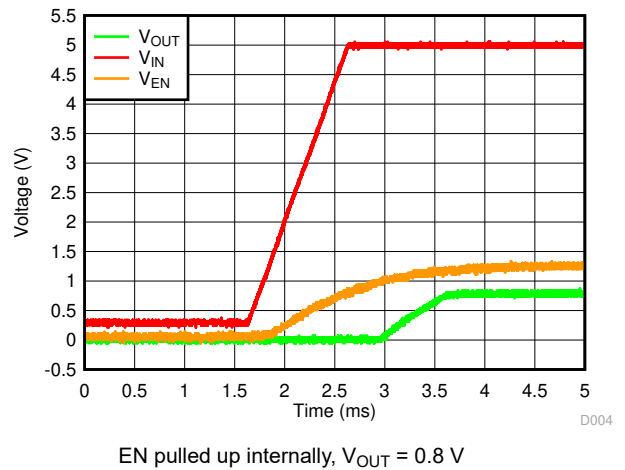
6-19. Foldback Current Limit vs I_{OUT} and Temperature



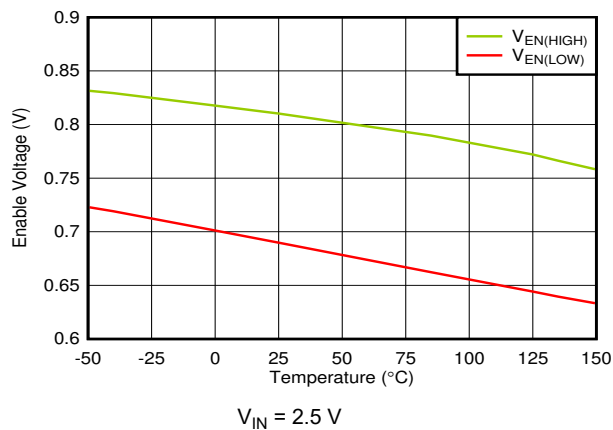
6-20. Foldback Current Limit vs I_{OUT} and Temperature



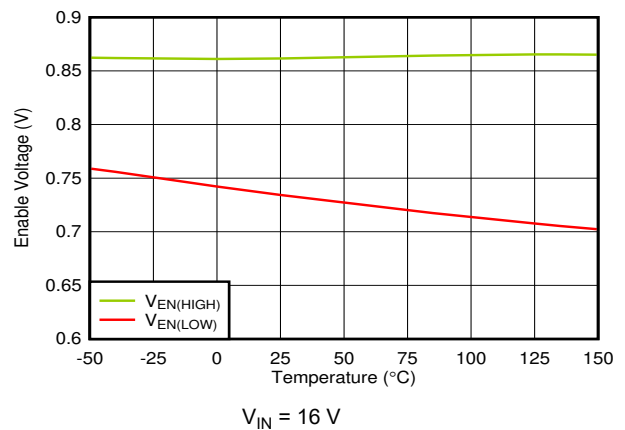
6-21. Startup With Separate V_{EN} and V_{IN}



6-22. Startup With V_{EN} Floating



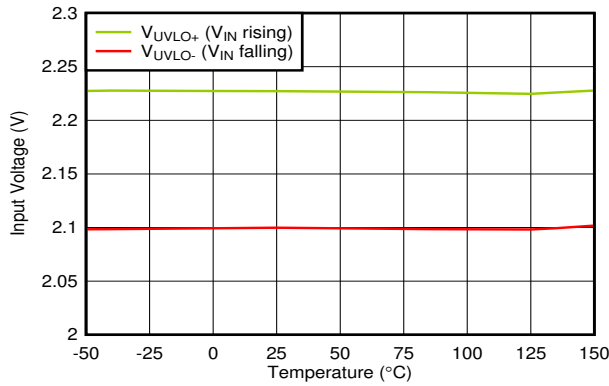
6-23. V_{EN} Thresholds vs Temperature



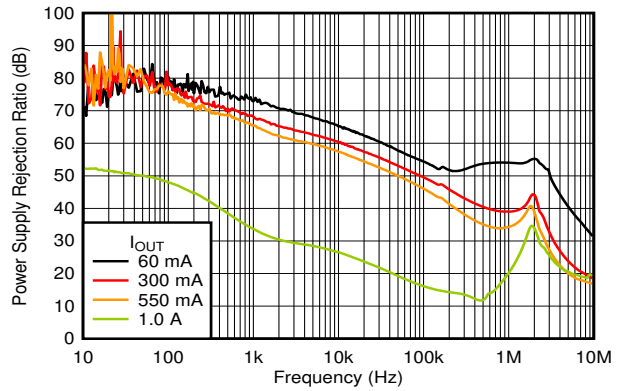
6-24. V_{EN} Thresholds vs Temperature

6.6 Typical Characteristics (continued)

at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)

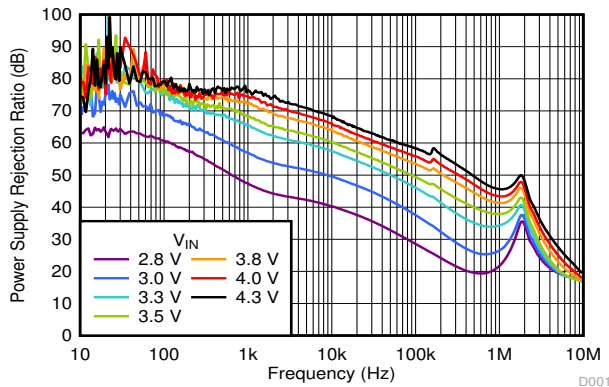


6-25. UVLO Thresholds vs Temperature



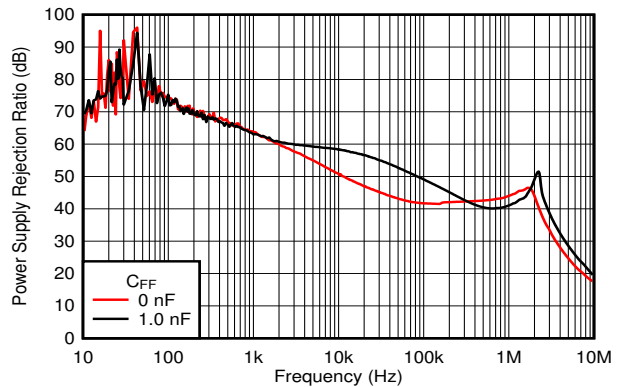
$V_{OUT} = 1.8\text{ V}$, $V_{IN} = 3.3\text{ V}$, $C_{FF} = 1\text{ nF}$

6-26. PSRR vs Frequency and I_{OUT}



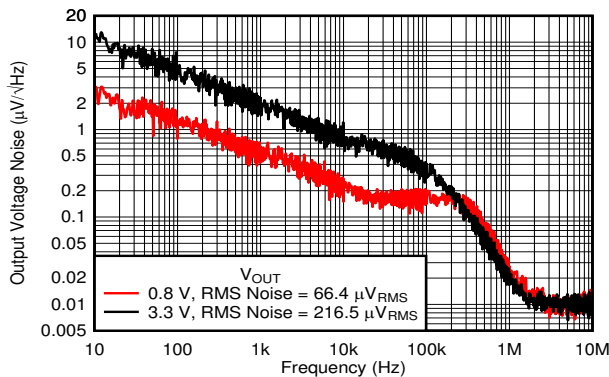
$V_{OUT} = 1.8\text{ V}$, $I_{OUT} = 0.55\text{ A}$, $C_{FF} = 1\text{ nF}$

6-27. PSRR vs Frequency and V_{IN}



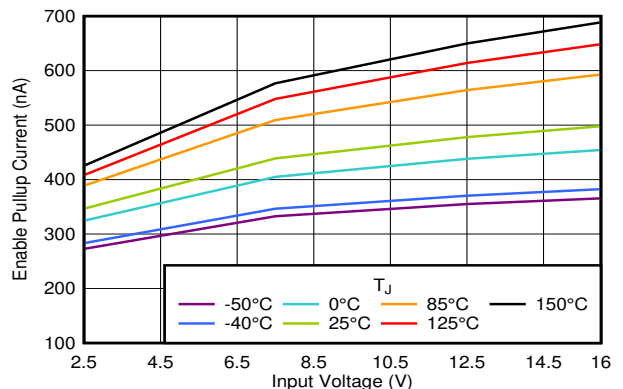
$V_{OUT} = 3.3\text{ V}$, $V_{IN} = 4.8\text{ V}$, $I_{OUT} = 0.33\text{ A}$

6-28. PSRR vs Frequency and C_{FF}



$C_{FF} = 0\text{ nF}$, $I_{OUT} = 0.1\text{ A}$, RMS noise BW = 10 Hz to 100 kHz

6-29. Output Noise (V_n) vs Frequency and V_{OUT}

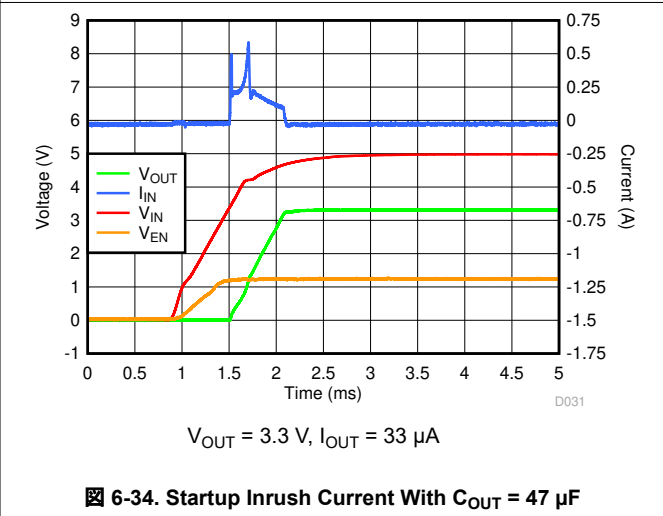
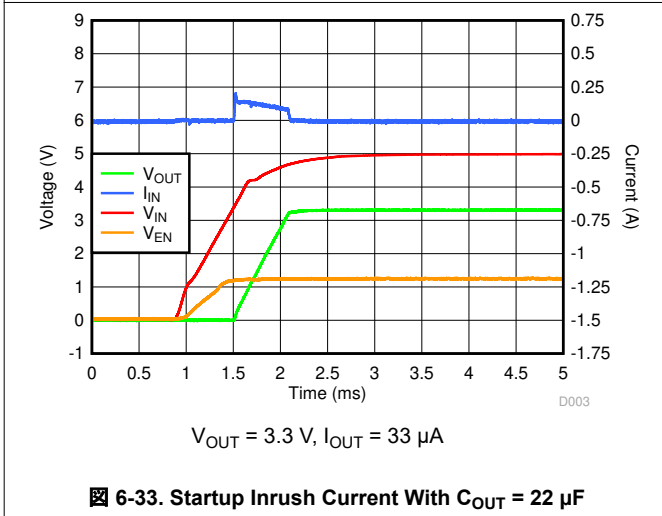
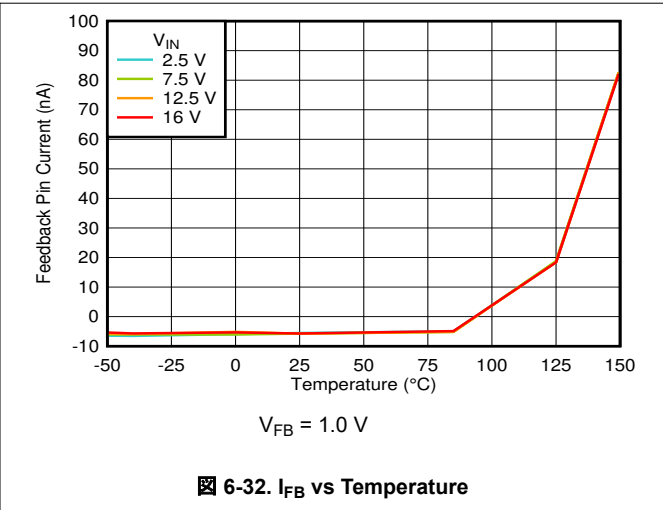
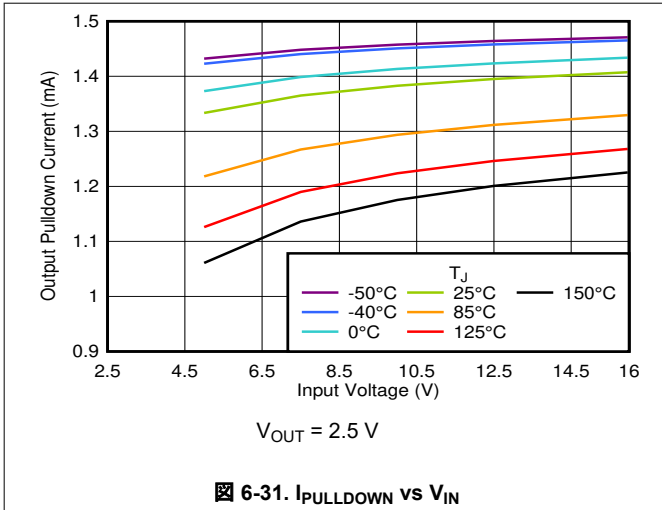


$V_{EN} = 0\text{ V}$

6-30. I_{EN} vs V_{IN}

6.6 Typical Characteristics (continued)

at operating temperature $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(NOM)} + 1.5\text{ V}$ or 2.5 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = 2.0\text{ V}$, $C_{IN} = 1.0\text{ }\mu\text{F}$, and $C_{OUT} = 1.0\text{ }\mu\text{F}$ (unless otherwise noted)



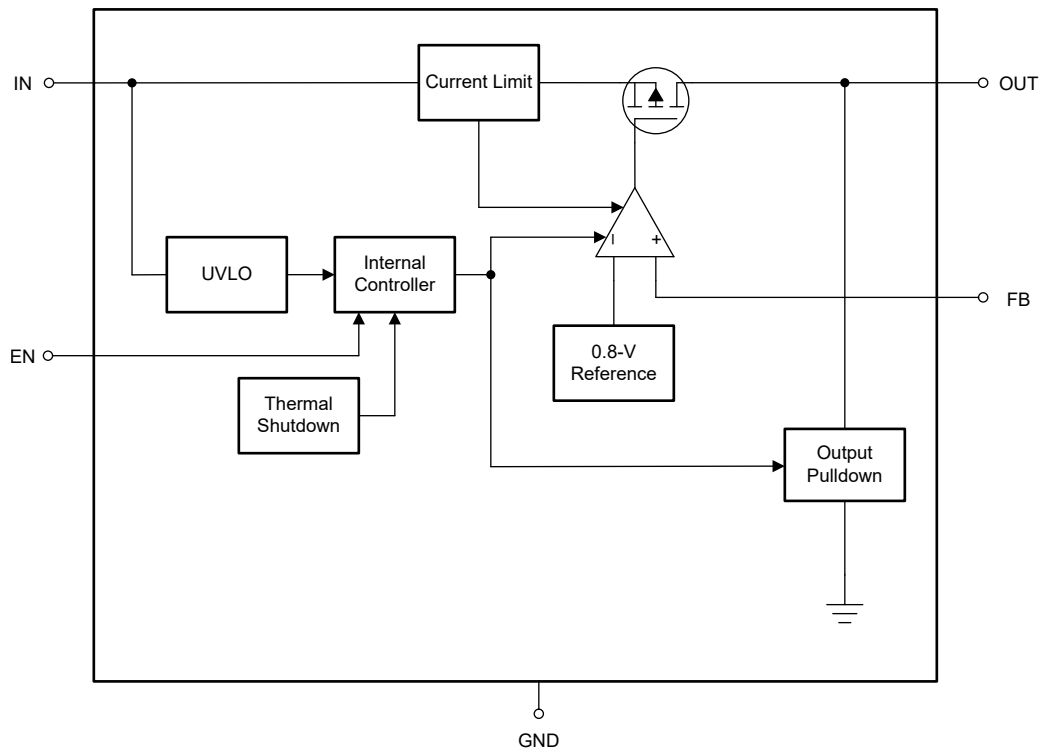
7 Detailed Description

7.1 Overview

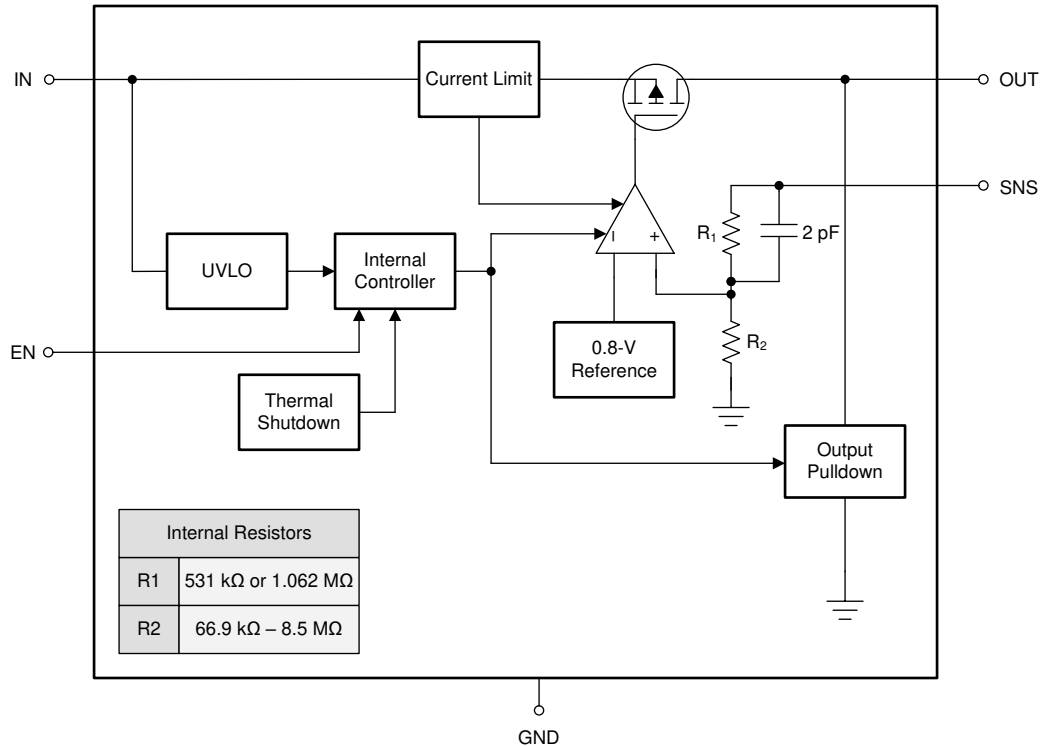
The TLV767-Q1 is a low quiescent current, high PSRR linear regulator capable of handling up to 1 A of load current. Unlike typical high current linear regulators, the TLV767-Q1 consumes significantly less quiescent current. This device is ideal for high current applications that require very sensitive power-supply rails.

This device features an integrated foldback current limit, thermal shutdown, output enable, internal output pulldown, and undervoltage lockout (UVLO). This device delivers excellent line and load transient performance. This device is low noise and exhibits very good PSRR. The operating ambient temperature range of the device is -40°C to $+125^{\circ}\text{C}$.

7.2 Functional Block Diagrams



7-1. Adjustable-Version Block Diagram



7-2. Fixed-Version Block Diagram

7.3 Feature Description

7.3.1 Output Enable

The enable pin for the device is an active-high pin. The output voltage is enabled when the voltage of the enable pin is greater than the high-level input voltage of the EN pin and disabled when the enable pin voltage is less than the low-level input voltage of the EN pin. If independent control of the output voltage is not needed, connect the enable pin to the input of the device.

This device has an internal pullup current on the EN pin. The EN pin can be left floating to enable the device.

The device has an internal pulldown circuit that activates when the device is disabled to actively discharge the output voltage.

7.3.2 Dropout Voltage

Dropout voltage (V_{DO}) is defined as the input voltage minus the output voltage ($V_{IN} - V_{OUT}$) at the rated output current (I_{RATED}), where the pass transistor is fully on. I_{RATED} is the maximum I_{OUT} listed in the *Recommended Operating Conditions* table. The pass transistor is in the ohmic or triode region of operation, and acts as a switch. The dropout voltage indirectly specifies a minimum input voltage greater than the nominal programmed output voltage at which the output voltage is expected to stay in regulation. If the input voltage falls to less than the nominal output regulation, then the output voltage falls as well.

For a CMOS regulator, the dropout voltage is determined by the drain-source on-state resistance ($R_{DS(ON)}$) of the pass transistor. Therefore, if the linear regulator operates at less than the rated current, the dropout voltage for that current scales accordingly. The following equation calculates the $R_{DS(ON)}$ of the device.

$$R_{DS(ON)} = \frac{V_{DO}}{I_{RATED}} \quad (1)$$

7.3.3 Foldback Current Limit

The device has an internal current limit circuit that protects the regulator during transient high-load current faults or shorting events. The current limit is a hybrid brickwall-foldback scheme. The current limit transitions from a brickwall scheme to a foldback scheme at the foldback voltage ($V_{FOLDBACK}$). In a high-load current fault with the output voltage above $V_{FOLDBACK}$, the brickwall scheme limits the output current to the current limit (I_{CL}). When the voltage drops below $V_{FOLDBACK}$, a foldback current limit activates that scales back the current as the output voltage approaches GND. When the output is shorted, the device supplies a typical current called the short-circuit current limit (I_{SC}). I_{CL} and I_{SC} are listed in the *Electrical Characteristics* table.

For this device, $V_{FOLDBACK} = 50\% \times V_{OUT(nom)}$.

The output voltage is not regulated when the device is in current limit. When a current limit event occurs, the device begins to heat up because of the increase in power dissipation. When the device is in brickwall current limit, the pass transistor dissipates power $[(V_{IN} - V_{OUT}) \times I_{CL}]$. When the device output is shorted and the output is below $V_{FOLDBACK}$, the pass transistor dissipates power $[(V_{IN} - V_{OUT}) \times I_{SC}]$. If thermal shutdown is triggered, the device turns off. After the device cools down, the internal thermal shutdown circuit turns the device back on. If the output current fault condition continues, the device cycles between current limit and thermal shutdown. For more information on current limits, see the [Know Your Limits application report](#).

Figure 7-3 shows a diagram of the foldback current limit.

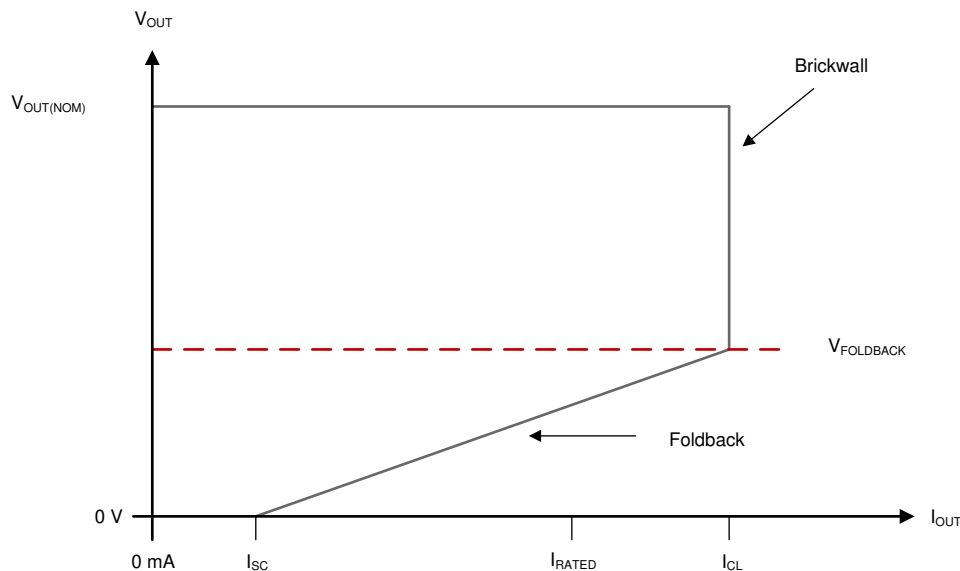


Figure 7-3. Foldback Current Limit

7.3.4 Undervoltage Lockout (UVLO)

The device has an independent undervoltage lockout (UVLO) circuit that monitors the input voltage, allowing a controlled and consistent turn on and off of the output voltage. To prevent the device from turning off if the input drops during turn on, the UVLO has hysteresis as specified in the *Electrical Characteristics* table.

7.3.5 Output Pulldown

The device has an output pulldown circuit. V_{OUT} pulldown sink to ground capability is listed in the *Electrical Characteristics* table. The output pulldown activates under the following conditions:

- Device disabled
- $1.0\text{ V} < V_{IN} < V_{UVLO}$

The output pulldown current for this device is 1.2 mA typical, as listed in the *Electrical Characteristics* table of the [Specifications](#) section.

Do not rely on the output pulldown circuit for discharging a large amount of output capacitance after the input supply has collapsed because reverse current can flow from the output to the input. This reverse current flow can cause damage to the device. See the *Reverse Current* section for more details.

7.3.6 Thermal Shutdown

The device contains a thermal shutdown protection circuit to disable the device when the junction temperature (T_J) of the pass transistor rises to $T_{SD(\text{shutdown})}$ (typical). Thermal shutdown hysteresis assures that the device resets (turns on) when the temperature falls to $T_{SD(\text{reset})}$ (typical).

The thermal time-constant of the semiconductor die is fairly short, thus the device may cycle on and off when thermal shutdown is reached until power dissipation is reduced. Power dissipation during startup can be high from large $V_{IN} - V_{OUT}$ voltage drops across the device or from high inrush currents charging large output capacitors. Under some conditions, the thermal shutdown protection disables the device before startup completes.

For reliable operation, limit the junction temperature to the maximum listed in the *Recommended Operating Conditions* table. Operation above this maximum temperature causes the device to exceed its operational specifications. Although the internal protection circuitry of the device is designed to protect against thermal overall conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the device into thermal shutdown or above the maximum recommended junction temperature reduces long-term reliability.

7.4 Device Functional Modes

7.4.1 Device Functional Mode Comparison

The *Device Functional Mode Comparison* table shows the conditions that lead to the different modes of operation. See the *Electrical Characteristics* table for parameter values.

表 7-1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER			
	V_{IN}	V_{EN}	I_{OUT}	T_J
Normal operation	$V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$	$V_{EN} > V_{EN(HI)}$	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$
Dropout operation	$V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{EN(HI)}$	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$
Disabled (any true condition disables the device)	$V_{IN} < V_{UVLO}$	$V_{EN} < V_{EN(LOW)}$	Not applicable	$T_J > T_{SD(shutdown)}$

7.4.2 Normal Operation

The device regulates to the nominal output voltage when the following conditions are met:

- The input voltage is greater than the set MID_OUT output voltage plus the V_{MID_OUT} dropout voltage ($V_{MID_OUT(nom)} + V_{DO(MID_OUT)}$)
- The current sourced from OUT or MID_OUT is less than the current limits ($I_{OUT} < I_{CL(OUT)}$ or $I_{MID_OUT} < I_{CL(MID_OUT)}$) respectively
- The device junction temperature is less than the thermal shutdown temperature ($T_J < T_{SD}$)
- The enable voltage has previously exceeded the enable rising threshold voltage and has not yet decreased to less than the enable falling threshold or the EN pin is left floating

7.4.3 Dropout Operation

If the input voltage is lower than the set MID_OUT voltage plus the specified $V_{DO(MID_OUT)}$ dropout voltage, but all other conditions are met for normal operation, the device operates in V_{MID_OUT} dropout mode. When the device operates in this mode while V_{MID_OUT} voltage is still higher than $V_{OUT(nom)} + V_{DO(OUT)}$, then V_{OUT} is still in regulation however V_{MID_OUT} voltage is in its dropout mode. In V_{MID_OUT} dropout mode, V_{MID_OUT} voltage tracks the input voltage and during this mode, the transient performance of V_{MID_OUT} voltage becomes significantly degraded because the MID_OUT pass transistor is in the ohmic or triode region, and acts as a switch. Also V_{MID_OUT} line or load transients can result in large V_{MID_OUT} voltage deviations.

The device enters $V_{DO(OUT)}$ dropout mode when the input voltage is lower than the set MID_OUT voltage and V_{MID_OUT} is lower than $V_{OUT(nom)} + V_{DO(OUT)}$. In V_{OUT} dropout mode, V_{OUT} voltage tracks V_{MID_OUT} voltage which in return tracks the input voltage. During this mode, the transient performance of both V_{MID_OUT} and V_{OUT} voltages becomes significantly degraded because the pass transistors are in the ohmic or triode region and acting as switches. Also line or load transients can result in large V_{MID_OUT} and V_{OUT} voltages deviations.

When the device is in a steady dropout state (defined as when the device is in dropout, $V_{IN} < V_{OUT(NOM)} + V_{DO}$, directly after being in a normal regulation state, but *not* during startup), the pass transistor is driven into the ohmic or triode region. When the input voltage returns to a value greater than or equal to the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$), the output voltage can overshoot for a short period of time while the device pulls the pass transistor back into the linear region.

7.4.4 Disabled

The output of the device can be shutdown by forcing the voltage of the enable pin to less than the maximum EN pin low-level input voltage (see the *Electrical Characteristics* table). When disabled, the pass transistor is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground by an internal discharge circuit from the output to ground.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Adjustable Device Feedback Resistors

The adjustable-version device requires external feedback divider resistors to set the output voltage. V_{OUT} is set using the feedback divider resistors, R_1 and R_2 , according to the following equation:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \quad (2)$$

To ignore the FB pin current error term in the V_{OUT} equation, set the feedback divider current to 100x the FB pin current listed in the *Electrical Characteristics* table. This setting provides the maximum feedback divider series resistance, as shown in the following equation:

$$R_1 + R_2 \leq V_{OUT} / (I_{FB} \times 100) \quad (3)$$

8.1.2 Recommended Capacitor Types

The device is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input and output. Multilayer ceramic capacitors have become the industry standard for these types of applications and are recommended, but must be used with good judgment. Ceramic capacitors that employ X7R-, X5R-, and C0G-rated dielectric materials provide relatively good capacitive stability across temperature, whereas the use of Y5V-rated capacitors is discouraged because of large variations in capacitance.

Regardless of the ceramic capacitor type selected, the effective capacitance varies with operating voltage and temperature. As a rule of thumb, expect the effective capacitance to decrease by as much as 50%. The input and output capacitors recommended in the *Recommended Operating Conditions* table account for an effective capacitance of approximately 50% of the nominal value.

8.1.3 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability, good analog design practice is to connect a capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. An input capacitor is recommended if the source impedance is more than 0.5 Ω . A higher value capacitor may be necessary if large, fast rise-time load or line transients are anticipated or if the device is located several inches from the input power source.

Dynamic performance of the device is improved with the use of an output capacitor. Use an output capacitor within the range specified in the *Recommended Operating Conditions* table for stability.

8.1.4 Reverse Current

Excessive reverse current can damage this device. Reverse current flows through the intrinsic body diode of the pass transistor instead of the normal conducting channel. At high magnitudes, this current flow degrades the long-term reliability of the device.

Conditions where reverse current can occur are outlined in this section, all of which can exceed the absolute maximum rating of $V_{OUT} \leq V_{IN} + 0.3$ V.

- If the device has a large C_{OUT} and the input supply collapses with little or no load current
- The output is biased when the input supply is not established
- The output is biased above the input supply

If reverse current flow is expected in the application, external protection is recommended to protect the device. Reverse current is not limited in the device, so external limiting is required if extended reverse voltage operation is anticipated.

Figure 8-1 shows one approach for protecting the device.

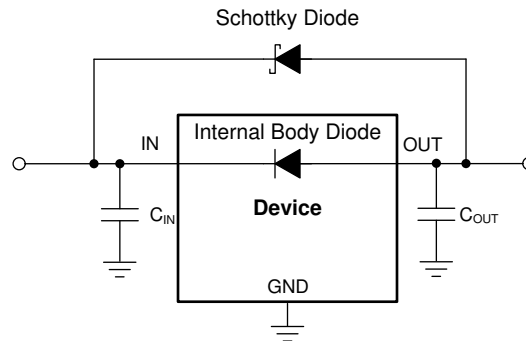


Figure 8-1. Example Circuit for Reverse Current Protection Using a Schottky Diode

8.1.5 Feed-Forward Capacitor (C_{FF})

For the adjustable-voltage version device, a feed-forward capacitor (C_{FF}) can be connected from the OUT pin to the FB pin. C_{FF} improves transient, noise, and PSRR performance, but is not required for regulator stability. Recommended C_{FF} values are listed in the *Recommended Operating Conditions* table. A higher capacitance C_{FF} can be used; however, the startup time increases. For a detailed description of C_{FF} tradeoffs, see the [Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator application report](#).

C_{FF} and R_1 form a zero in the loop gain at frequency f_z , while C_{FF} , R_1 , and R_2 form a pole in the loop gain at frequency f_p . C_{FF} zero and pole frequencies can be calculated from the following equations:

$$f_z = 1 / (2 \times \pi \times C_{FF} \times R_1) \quad (4)$$

$$f_p = 1 / (2 \times \pi \times C_{FF} \times (R_1 \parallel R_2)) \quad (5)$$

$C_{FF} \geq 10$ pF is required for stability if the feedback divider current is less than 5 μ A. Equation 6 calculates the feedback divider current.

$$I_{FB_Divider} = V_{OUT} / (R_1 + R_2) \quad (6)$$

To avoid startup time increases from C_{FF} , limit the product $C_{FF} \times R_1 < 50$ μ s.

For an output voltage of 0.8 V with the FB pin tied to the OUT pin, no C_{FF} is used.

8.1.6 Power Dissipation (P_D)

Circuit reliability requires consideration of the device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must have few or no other heat-generating devices that cause added thermal stress.

To first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. The following equation calculates power dissipation (P_D).

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (7)$$

Note

Power dissipation can be minimized, and therefore greater efficiency can be achieved, by correct selection of the system voltage rails. For the lowest power dissipation use the minimum input voltage required for correct output regulation.

For devices with a thermal pad, the primary heat conduction path for the device package is through the thermal pad to the PCB. Solder the thermal pad to a copper pad area under the device. This pad area must contain an array of plated vias that conduct heat to additional copper planes for increased heat dissipation.

The maximum power dissipation determines the maximum allowable ambient temperature (T_A) for the device. According to the following equation, power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T_A).

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad (8)$$

Thermal resistance ($R_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The junction-to-ambient thermal resistance listed in the *Thermal Information* table is determined by the JEDEC standard PCB and copper-spreading area, and is used as a relative measure of package thermal performance.

8.1.7 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi (Ψ) thermal metrics to estimate the junction temperatures of the linear regulator when in-circuit on a typical PCB board application. These metrics are not thermal resistance parameters and instead offer a practical and relative way to estimate junction temperature. These psi metrics are determined to be significantly independent of the copper area available for heat-spreading. The *Thermal Information* table lists the primary thermal metrics, which are the junction-to-top characterization parameter (ψ_{JT}) and junction-to-board characterization parameter (ψ_{JB}). These parameters provide two methods for calculating the junction temperature (T_J), as described in the following equations. Use the junction-to-top characterization parameter (ψ_{JT}) with the temperature at the center-top of device package (T_T) to calculate the junction temperature. Use the junction-to-board characterization parameter (ψ_{JB}) with the PCB surface temperature 1 mm from the device package (T_B) to calculate the junction temperature.

$$T_J = T_T + \psi_{JT} \times P_D \quad (9)$$

where:

- P_D is the dissipated power
- T_T is the temperature at the center-top of the device package

$$T_J = T_B + \psi_{JB} \times P_D \quad (10)$$

where:

- T_B is the PCB surface temperature measured 1 mm from the device package and centered on the package edge

For detailed information on the thermal metrics and how to use them, see the [Semiconductor and IC Package Thermal Metrics application report](#)

8.2 Typical Application

This section discusses implementing this device for a typical application. [Figure 8-2](#) shows the application circuit.

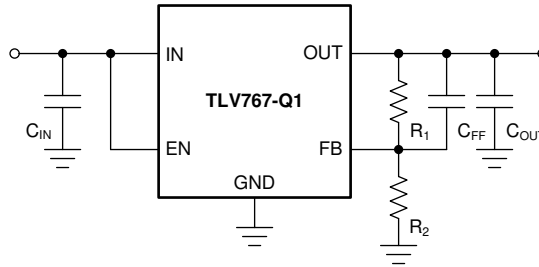


Figure 8-2. Typical Application Circuit

8.2.1 Design Requirements

[Table 8-1](#) summarizes the design requirements for this application.

Table 8-1. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	5 V
Output voltage	3.3 V
Output current	100 mA

8.2.2 Detailed Design Procedure

8.2.2.1 Transient Response

As with any regulator, increasing the size of the output capacitor reduces overshoot and undershoot magnitude. If load transients are expected with ramp rates greater than 0.5 A/μs, use a 2.2-μF or larger output capacitor.

8.2.2.2 Choose Feedback Resistors

For this design example, V_{OUT} is set to 3.3 V. The following equations set the feedback divider resistors for the desired output voltage:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \quad (11)$$

$$R_1 + R_2 \leq V_{OUT} / (I_{FB} \times 100) \quad (12)$$

For improved output accuracy, use [Equation 12](#) and $I_{FB} = 50$ nA as listed in the *Electrical Characteristics* table in the [Specifications](#) section to calculate the upper limit for series feedback resistance ($R_1 + R_2 \leq 660$ kΩ).

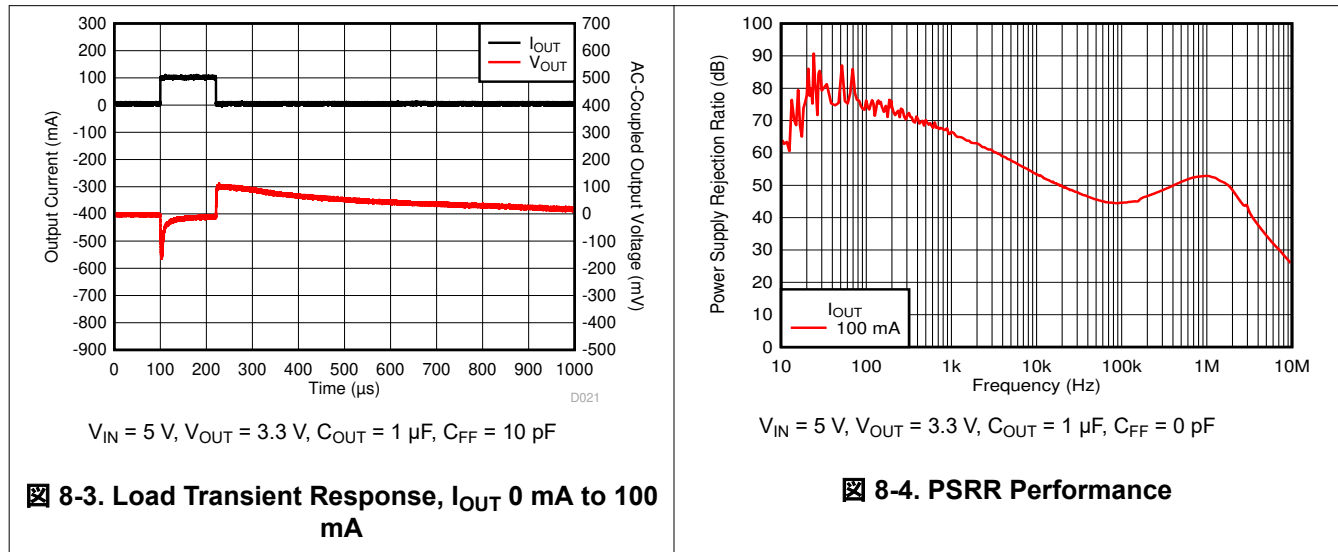
The control-loop error amplifier drives the FB pin to the same voltage as the internal reference ($V_{FB} = 0.8$ V, as listed in the *Electrical Characteristics* table). Use [Equation 11](#) to determine the ratio of $R_1 / R_2 = 3.125$. Use this ratio and solve [Equation 12](#) for R_2 . Now calculate the upper limit for $R_2 \leq 160$ kΩ. Select a standard value resistor for $R_2 = 160$ kΩ.

Reference [Equation 11](#) and solve for R_1 :

$$R_1 = (V_{OUT} / V_{FB} - 1) \times R_2 \quad (13)$$

From [Equation 13](#), $R_1 = 500$ kΩ can be determined. Select a standard value resistor for $R_1 = 499$ kΩ. $V_{OUT} = 3.3$ V (as determined by [Equation 11](#)).

8.2.3 Application Curves



9 Power Supply Recommendations

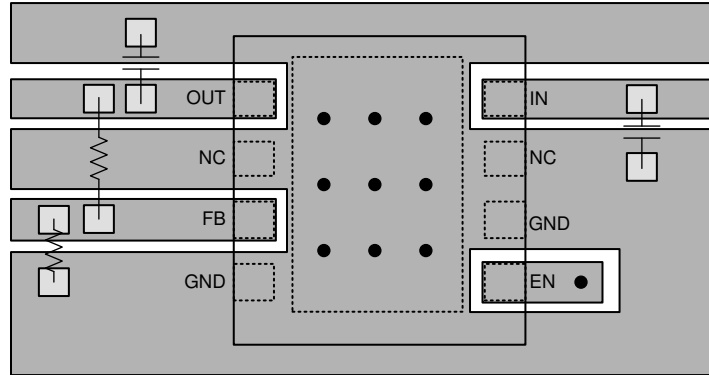
This device is designed to operate from an input supply voltage range of 2.5 V to 16 V. To ensure that the output voltage is well regulated and dynamic performance is optimum, the input supply must be at least $V_{OUT(nom)} + 1.5\text{ V}$ or 2.5 V, whichever is greater. For a 1-A output current operation, the input supply must be 3 V or greater. Connect a low output impedance power supply directly to the input pin of the TLV767-Q1.

10 Layout

10.1 Layout Guidelines

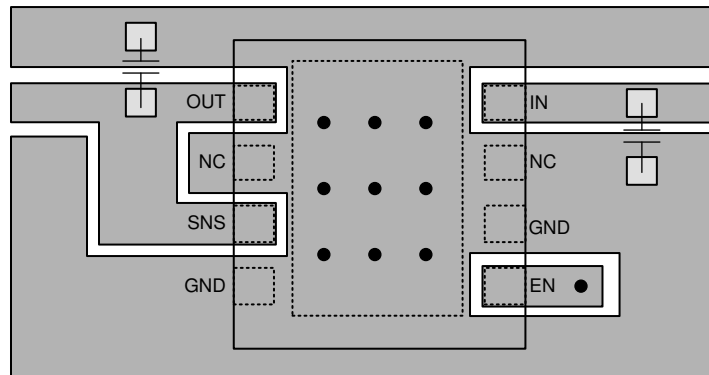
- Place input and output capacitors as close to the device as possible
- Use copper planes for device connections to IN, OUT, and GND pins to optimize thermal performance
- Place thermal vias around the device to distribute heat

10.2 Layout Examples



● Denotes a via

☒ 10-1. Layout Example for the Adjustable Version



● Denotes a via

☒ 10-2. Layout Example for the Fixed Version

11 Device and Documentation Support

11.1 Device Support

11.1.1 Device Nomenclature

表 11-1. Available Options ⁽¹⁾

PRODUCT	V _{OUT}
TLV767xx(x)QWyyyRQ1	<p>xx(x) is the nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number; otherwise, three digits are used (for example, 33 = 3.3 V; 125 = 1.25 V). 01 indicates the adjustable output version.</p> <p>W indicates a wettable flanks package.</p> <p>yyy is the package designator.</p> <p>R is the package quantity. R is for the large quantity reel.</p>

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [TLV767EVM-014 Evaluation Module user's guide](#)
- Texas Instruments, [Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator application report](#)
- Texas Instruments, [Know Your Limits application report](#)
- Texas Instruments, [Universal Low-Dropout \(LDO\) Linear Voltage Regulator MultiPkgLDOEVM-823 Evaluation Module user's guide](#)

11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.5 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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11.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV76701QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76701	Samples
TLV76733QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76733	Samples
TLV76750QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76750	Samples
TLV76760QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76760	Samples
TLV76780QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76780	Samples
TLV76790QWDRBRQ1	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	V76790	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV76701QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV76733QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV76750QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV76760QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV76780QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV76790QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV76701QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TLV76733QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TLV76750QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TLV76760QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TLV76780QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TLV76790QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0

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